DMA204A0

Silicon PNP epitaxial planar type

For low frequency amplification

■ Features

- \bullet Low collector-emitter saturation voltage $V_{\text{CE(sat)}}$
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

■ Basic Part Number

Dual DSA2401 (Individual)

■ Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	-15	V
Collector-emitter voltage (Base open)	V _{CEO}	-10	V
Emitter-base voltage (Collector open)	V_{EBO}	-7	V
Collector current	I_{C}	-0.5	A
Peak collector current	I _{CP}	-1	A
Total power dissipation	P _T	300	mW
Junction temperature	T_{j}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Package

• Code

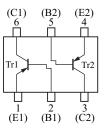
Mini6-G4-B

Pin Name

1: Emitter (Tr1) 4: Emitter (Tr2) 2: Base (Tr1) 5: Base (Tr2) 3: Collector (Tr2) 6: Collector (Tr1)

■ Marking Symbol: C0

■ Internal Connection



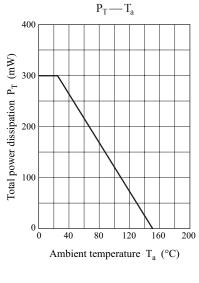
■ Electrical Characteristics $T_a = 25$ °C±3°C

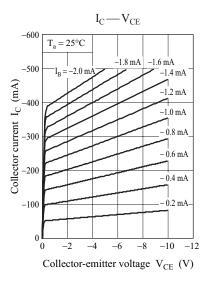
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_{\rm C} = -10 \mu\text{A}, I_{\rm E} = 0$	-15			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = -1 \text{ mA}, I_B = 0$	-10			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \mu\text{A}, I_C = 0$	-7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -10 \text{ V}, I_E = 0$			-100	nA
Forward current transfer ratio *	h _{FE1}	$V_{CE} = -2 \text{ V}, I_{C} = -0.5 \text{ A}$	130		350	
	h _{FE2}	$V_{CE} = -2 \text{ V}, I_{C} = -1 \text{ A}$	60			
Collector-emitter saturation voltage *	V _{CE(sat)}	$I_C = -0.4 \text{ A}, I_B = -8 \text{ mA}$		-0.15	-0.30	V
Base-emitter saturation voltage *	V _{BE(sat)}	$I_C = -0.4 \text{ A}, I_B = -8 \text{ mA}$		- 0.8	-1.2	V
Transition frequency	f_T	$V_{CE} = -10 \text{ V}, I_{C} = -50 \text{ mA}$		250		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		18		pF

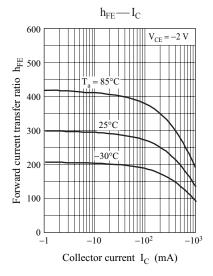
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

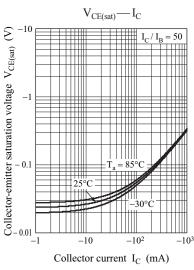
2. *: Pulse measurement

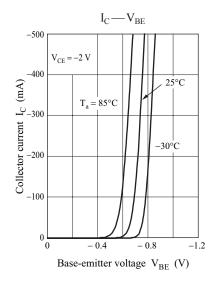
DMA204A0 Panasonic

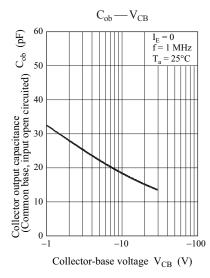


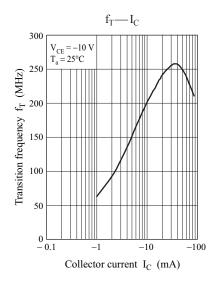


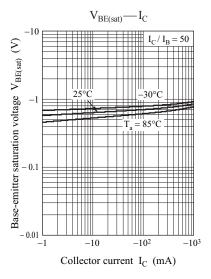






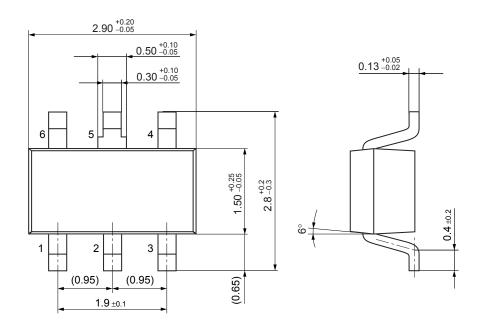


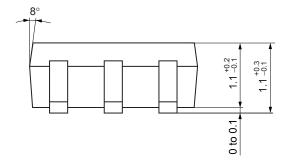




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Mini6-G4-B Unit: mm





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